



STS3DNE60L

N - CHANNEL 60V - 0.065Ω - 3A SO-8 STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STS3DNE60L	60 V	< 0.08 Ω	3 A

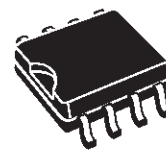
- TYPICAL R_{DS(on)} = 0.065 Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique " Single Feature Size™ " strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

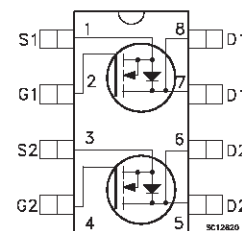
APPLICATIONS

- DC MOTOR DRIVE
- DC-DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT
- POWER MANAGEMENT IN PORTABLE/DESKTOP PCs



SO-8

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C Single Operation	3	A
	Drain Current (continuous) at T _c = 100 °C Single Operation	1.9	A
I _{DM} (•)	Drain Current (pulsed)	12	A
P _{tot}	Total Dissipation at T _c = 25 °C Dual Operation	2	W
	Total Dissipation at T _c = 25 °C Single Operation	1.6	W

(•) Pulse width limited by safe operating area

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THERMAL DATA

$R_{thj-amb}$	*Thermal Resistance Junction-ambient	Single Operation Dual Operation	78 62.5	$^{\circ}\text{C/W}$ $^{\circ}\text{C/W}$
T_j	Maximum Operating Junction Temperature		175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-55 to 150	$^{\circ}\text{C}$

(*) Mounted on FR-4 board ($t \leq 10\text{sec}$)

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ $V_{GS} = 0$	60			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ \text{V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu\text{A}$	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\ \text{V}$ $I_D = 1.5\ \text{A}$ $V_{GS} = 4.5\ \text{V}$ $I_D = 1.5\ \text{A}$		0.065 0.08	0.08 0.1	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\ \text{V}$	3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.5\ \text{A}$		5		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\ \text{V}$ $f = 1\ \text{MHz}$ $V_{GS} = 0\ \text{V}$		815 125 40		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30\text{ V}$ $I_D = 10\text{ A}$		20		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Resistive Load, see fig. 3)		45		ns
Q_g	Total Gate Charge	$V_{DD} = 24\text{ V}$ $I_D = 3\text{ A}$ $V_{GS} = 4.5\text{ V}$		13.5	18	nC
Q_{gs}	Gate-Source Charge			8		nC
Q_{gd}	Gate-Drain Charge			3.5		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 30\text{ V}$ $I_D = 10\text{ A}$		40		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Resistive Load, see fig. 3)		10		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 48\text{ V}$ $I_D = 20\text{ A}$		10		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		25		ns
t_c	Cross-over Time	(Inductive Load, see fig. 5)		42		ns

SOURCE DRAIN DIODE

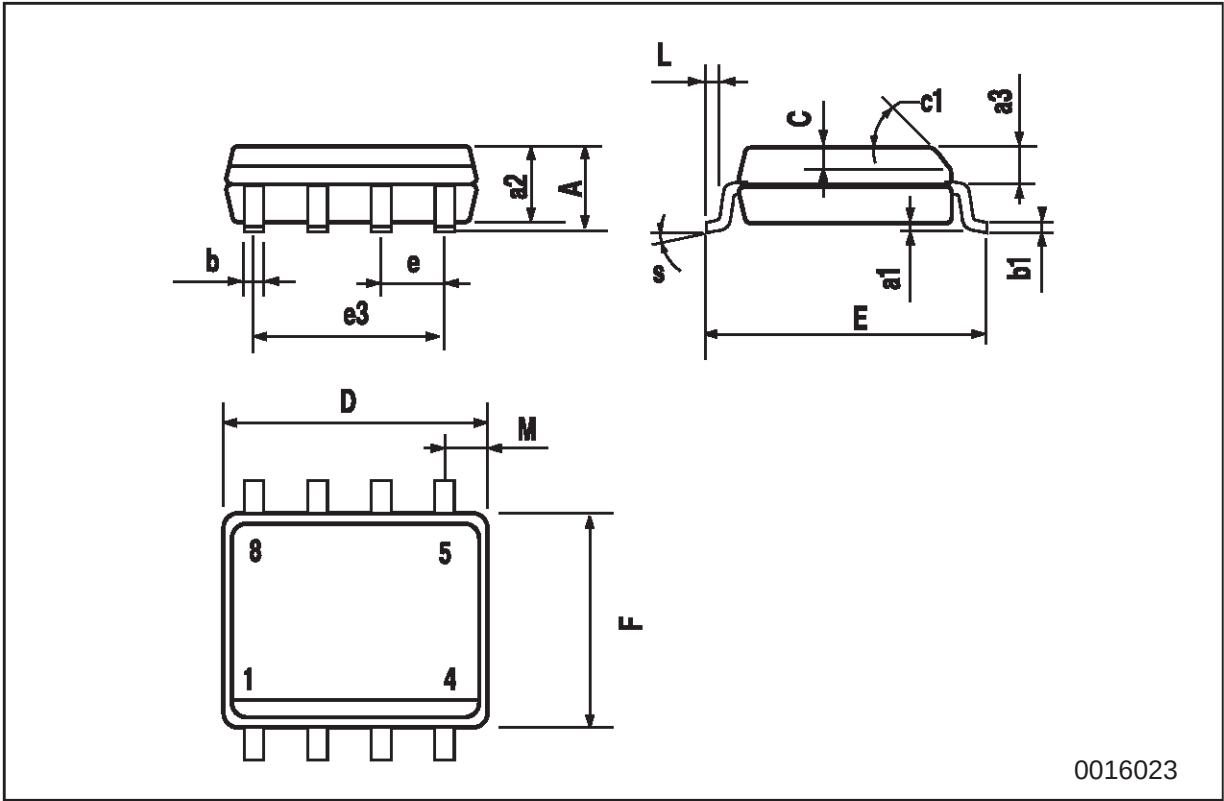
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				3	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				12	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 3\text{ A}$ $V_{GS} = 0$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 20\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$ (see test circuit, fig. 5)		65		ns
Q_{rr}	Reverse Recovery Charge			130		nC
I_{RRM}	Reverse Recovery Current			4		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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